

		Type	L #	Hits	Search Text	DBs	Time Stamp	Cor ro mm en ts	De ni ti on	Er ro rs
1	BRS	L3	3		dop\$3 with (semiconductor or silicon) same (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and bur\$5 near oxide with epitaxial\$2 with (heat\$4 or thermal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 12:42			
2	BRS	L4	4		dop\$3 with (semiconductor or silicon) and (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and bur\$5 near oxide with epitaxial\$2 with (heat\$4 or thermal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 12:43			

				Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r Co mm en ts	De fi ni ti on	Er ro r Co mm en ts
3	BRS	L8	0				(438/542).ccls. and (\$3MOS near transistor or mosfet) and dop\$3 with (semiconductor or silicon) same (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and oxide with epitaxial\$2 with (heat\$4 or thermal\$4)	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:38				

				Type	L #	Hits	Search Text	DBs	Time Stamp	Cor ro mm en ts	De fi ni ti on	Er ro rs
4	BRS	L9	1				(438/308).ccls. and (\$3MOS near transistor or mosfet) and dop\$3 with (semiconductor or silicon) same (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and oxide with epitaxial\$2 with (heat\$4 or thermal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 12:52			

				Type	L #	Hits	Search Text	DBs	Time Stamp	Comm en ts	Cor re cti on	Defi ni ti on	Er ro rs
5	BRS	L10	7				(438/309).ccls. and (\$3MOS near transistor or mosfet) and dop\$3 with (semiconductor or silicon) same (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and oxide with epitaxial\$2 with (heat\$4 or thermal\$4)	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 12:56				

								Er ro r Co mm en ts	Er ro r De ni ti on
	Type	L #	Hits	Search Text	DBs	Time Stamp			
6	BRS	L11	76	("438"/\$).ccls. and (MOS near transistor or mosfet) and dop\$3 with (semiconductor or silicon or substrate) with surface same (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and oxide with epitaxial\$2 with (heat\$4 or thermal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 12:57			

				Type	L #	Hits	Search Text	DBs	Time Stamp	Cor r em en ts	De fi ni ti on	Er ro rs
7	BRS	L12	91				("438"/\$).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) with surface same (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and oxide with epitaxial\$2 with (heat\$4 or thermal\$4)	US-PPGUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:00			

								Co mm en ts	Er ro r m De ni ti on	Er ro r s
	Type	L #	Hits	Search Text	DBs	Time Stamp				
8	BRS	L13	72	("438"/\$).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) with surface same (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and oxide with epitaxial\$2 with (heat\$4 or thermal\$4) and @AD < "20011207"	US-PPGUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:07				

				Type	L #	Hits	Search Text	DBs	Time Stamp	Cor r em en ts	De fi ni ti on	Er ro rs
9	BRS	L14	4				("438"/\$).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) with surface same (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and bur\$4 with dop\$4 with epitaxial\$2 with (heat\$4 or thermal\$4) and @AD < "20011207"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:13			

								Co mm en ts	Er ro r m De en ni ti on	Er ro r s
	Type	L #	Hits	Search Text	DBs	Time Stamp				
10	BRS	L15	3	("438"/\$).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) with surface same (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and bur\$4 with dop\$4 with (form\$4 or produc\$4) with epitaxial\$2 with (heat\$4 or thermal\$4)	US-PPGUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:18				

				Type	L #	Hits	Search Text	DBs	Time Stamp	Cor r em en ts	Defi ni ti on	Er ro r or rs
11	BRS	L16	2				("438"/\$).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) with surface same (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and bur\$4 with dop\$4 with (form\$4 or produc\$4) with epitaxial\$2 with (heat\$4 or thermal\$4) and @AD<"20010712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:18			

	Type	L #	Hits	Search Text	DBs	Time Stamp		Er ro Co mm en ts	Er ro r De ni ti on		
12	BRS	L17	3	("438"/\$).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) with surface same (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and bur\$4 with dop\$4 with (form\$4 or produc\$4) with epitaxial\$2 with (heat\$4 or thermal\$4) and @AD < "20011207"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:23					

		Type	L #	Hits	Search Text	DBs	Time Stamp	Cor r ec tio ns	Er ro rs
13	BRS	L18	4		(MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) with surface same (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and bur\$4 with dop\$4 with (form\$4 or produc\$4) with epitaxial\$2 with (heat\$4 or thermal\$4) and @AD < "20011207"	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:27		

								Er ro r Co mm en ts	Er ro r De fi ni ti on	Er ro r rs
	Type	L #	Hits	Search Text	DBs	Time Stamp				
14	BRS	L21	1	(MOS or mosfet) and form\$3 with epitaxial\$2 with (heat\$4 or thermal\$4) and buried near doping and @AD < "20011207"	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:32				
15	BRS	L22	66	(MOS or mosfet) and form\$3 with epitaxial\$2 with (heat\$4 or thermal\$4) and buried with doping and @AD < "20011207"	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:32				

				Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error	Errors
16	BRS	L23	21				(MOS or mosfet) and form\$3 with epitaxial\$2 with (heat\$4 or thermal\$4) and buried with doping and (polycrysatalline or amorphous) and @AD < "20011207"	US-PPGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:33			
17	BRS	L28	2				((MOS or mosfet) and epitaxial\$2 with (heat\$4 or thermal\$4) and dop\$3 and (polycrysatalline or amorphous)).clm	US-PPGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:35			

								Er ro r Co mm en ts	Er ro r De fi ni ti on
	Type	L #	Hits	Search Text	DBs	Time Stamp			
18	BRS	L29	1	(438/542).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon) same (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:39			

				Type	L #	Hits	Search Text	DBs	Time Stamp	Cor r em en ts	De fi ni ti on	Er ro rs
19	BRS	L31	4				((MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4)).clm .	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:43			

								Er ro r Co mm en ts	Er ro r De ni ti on
	Type	L #	Hits	Search Text	DBs	Time Stamp			
20	BRS	L33	103	(MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:45			

	Type	L #	Hits	Search Text	DBs	Time Stamp					
21	BRS	L34	85	(MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:45					

				Type	L #	Hits	Search Text	DBs	Time Stamp	Cor r em en ts	De ni ti on	Er ro rs
22	BRS	L35	43				("438"/\$).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 14:05			

				Type	L #	Hits	Search Text	DBs	Time Stamp	Er ro Co mm en ts	r De ni ti on	Er ro rs		
23	BRS	L36	31				("4116720" "4454647" "4473598" "4520552" "4689871" "4745081" "4803535" "4816421" "4829017" "4847214" "4873560" "4910567" "4918502") .PN. OR ("5077228") .URP N.		US - PGPUB; USPAT; USOCR	2006/02/02 14:03				

				Type	L #	Hits	Search Text	DBs	Time Stamp	Cor r em en ts	De fi ni ti on	Er ro r Er ro rs
24	BRS	L37	0				(438/514).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 14:05			

				Type	L #	Hits	Search Text	DBs	Time Stamp	Cor mm en ts	Err or De en ti on	Er ro rs
25	BRS	L38	0				(438/482).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US-PPGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 14:05			

				Type	L #	Hits	Search Text	DBs	Time Stamp	Cor r ec tio ns	De fin iti on	Er ro rs
26	BRS	L39	0				(438/488).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 14:05			

				Type	L #	Hits	Search Text	DBs	Time Stamp	Comm en ts	Cor re cti on	De fin iti on	Er ro rs
27	BRS	L40	0				(438/506).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US-PPGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 14:05				

				Type	L #	Hits	Search Text	DBs	Time Stamp	Cor r em en ts	De fi ni ti on	Er ro r or rs
28	BRS	L41	0				(438/511).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 14:05			

				Type	L #	Hits	Search Text	DBs	Time Stamp	Cor ro mm en ts	De fi ni ti on	Er ro rs
29	BRS	L42	0				(438/522).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 14:06			

				Type	L #	Hits	Search Text	DBs	Time Stamp	Cor r ec tio n	De ni ti on	Er ro rs
30	BRS	L43	0				(438/526).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 14:06			

				Type	L #	Hits	Search Text	DBs	Time Stamp	Cor r em en ts	De fi ni ti on	Er ro rs
31	BRS	L44	0				(438/530).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 14:06			